



UPDATE CHANGE NOTIFICATION # 16512Generic Copy

Issue Date: 27-Oct-2011**TITLE:** Update Notification to Qualification of Additional Fab and Assembly Source for CM1213A-04SO, CM1293A-04SO**PROPOSED FIRST SHIP DATE:** 27-Oct-11**AFFECTED CHANGE CATEGORY(S):** Change to the Description and Purpose (Addendum)**ADDITIONAL RELIABILITY DATA:** Available
Contact your local ON Semiconductor Sales Office or Laura Rivers <laura.rivers@onsemi.com>**SAMPLES:** Contact your local ON Semiconductor Sales Office**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**
Contact your local ON Semiconductor Sales Office or Jill Daugherty <jill.daugherty@onsemi.com>**NOTIFICATION TYPE:**

Update Change Notification (UN)

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.**DESCRIPTION AND PURPOSE:**

This is an update to FPCN16512 submitted on 08/12/2010 to notify customer on the change in schematic diagram. Please refer to addendum below:

FPCN16512 announced that ON Semiconductor is qualifying an additional wafer source and an additional assembly site for CM1213A-04SO and CM1293A-04SO products. The additional wafer source will be ON Semiconductor's qualified Low Capacitance TVS process sourced from the ON Semiconductor COM1 Fab in Phoenix, US and the ON Semiconductor FAB2 in Oudenaarde, Belgium. The additional assembly site will be the Leshan assembly facility in Leshan, China, which is a joint venture between ON Semiconductor and Leshan Radio Company LTD.

The purpose of this change is to qualify a second product source in order to ensure continuous delivery of product to the customer.



UPDATE CHANGE NOTIFICATION #16512

Datasheet changes:

1. The Diode Forward Voltage (VF) specification will be changed in the following ways:
 - a. The min and max VF spec will be removed
 - b. The typ spec will be changed from 0.8V to 0.9V
 - c. The “Top Diode” and “Bottom Diode” differentiators will be removed
2. The Channel Input Capacitance (Cin) condition specified on the datasheet will be modified to match updated testing procedures: the Cin will be specified at Vin = 0V and freq = 1MHz. This testing condition is more rigorous than the current capacitance test specification.

Marking change:

CM1213A-04SO: marking will change from “D234” to “234”
 CM1293A-04SO: marking will change from “D635” to “635”

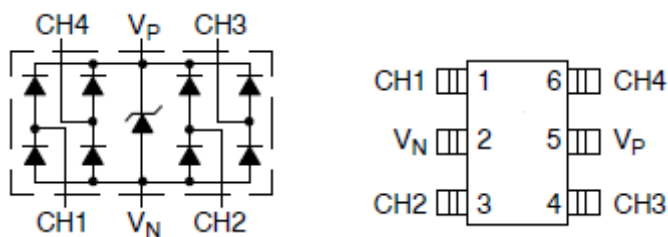
Additional changes:

1. The current CM1213A-04SO and CM1293A-04SO product uses Au wire. The product from the Leshan facility will use Cu wire.
2. The current package uses an epoxy die attach process. The product from the Leshan facility will use a eutectic die attach process.
3. The case outline for the two devices will be modified slightly to accommodate product from either assembly site.

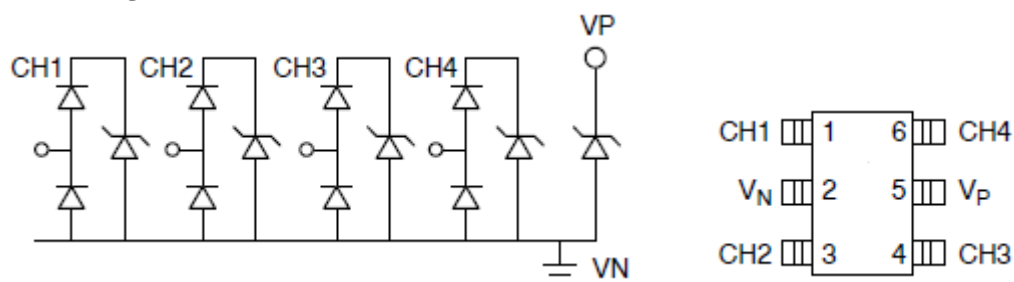
Addendum:

In order to facilitate certain parametric improvements during the transfer a change was made in the part schematic (shown below). This change is transparent in the performance of the part in the intended application, and the device pin out remains the same. However, the change may be noted during pin to pin ICT testing.

Pre-Change Schematic



Post-Change Schematic



**UPDATE CHANGE NOTIFICATION #16512****RELIABILITY DATA SUMMARY:**

Test:	Conditions:	Interval:	Results
HTRB	TA=150C,80% Rated Voltage	1008 hrs	0/252
Precondition	MSL1 @ 260C , 3 X IR at 260 C		0/1008
Autoclave+PC	Ta=121C RH=100% ~15 psig	96 hrs	0/252
H3TRB+PC	Ta=85C RH=85% bias=80% rated V 100V Max	1008 hrs	0/252
IOL+PC	Ta=25C, Delta TJ = 100 C, Ton/off = 2 min.	15000 cyc	0/252
TC+PC	Ta= -65 C to 150 C	1000 cyc	0/252
DPA Per AECQ101, after 1000 cyc TC			0/6
DPA Per AECQ101, after 1008 hrs H3TRB			0/6
RSH	Ta=260C, 10 sec dwell		0/30

ELECTRICAL CHARACTERISTIC SUMMARY: Available upon request

CHANGED PART IDENTIFICATION: Devices with date code marking of Y or later may be sourced from either factory

List of affected General Parts:

CM1213A-04SO
CM1293A-04SO